Vishay Siliconix

P-Channel 60 V (D-S), 175 °C MOSFET



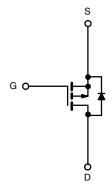
PRODUCT SUMMARY				
V _{DS} (V)	-60			
$R_{DS(on)}$ max. (Ω) at V_{GS} = -10 V	0.015			
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.020			
I _D (A) ^d	-50			
Configuration	Single			

FEATURES

- TrenchFET® power MOSFET
- 175 °C junction temperature



 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



P-Channel MOSFET

ORDERING INFORMATION		
Package	DPAK (TO-252)	
Lead (Pb)-free	SUD50P06-15L-E3	

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	-60	V
Gate-source voltage		V _{GS}	± 20	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Continuous drain current (T _J = 175 °C)	T _C = 25 °C		-50 ^d	
	T _C = 125 °C	I _D	-39	
Pulsed drain current		I _{DM}	-80	A
Avalanche current		I _{AR}	-50	
Repetitive avalanche energy ^a	L = 0.1 mH	E _{AR}	125	mJ
Davies discinsting	T _C = 25 °C	В	136 ^c	W
Power dissipation	T _A = 25 °C	P _D	3 b, c	
Operating junction and storage temperature range		Tı, Teta	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
lunation to ambient h	t ≤ 10 s	R_{thJA}	15	18	
Junction-to-ambient ^b	Steady state		40	50	°C/W
Junction-to-case		R _{thJC}	0.82	1.1	

Notes

- a. Duty cycle $\leq 1\%$
- b. When mounted on 1" square PCB (FR4 material)
- c. See SOA curve for voltage derating
- d. Package limited

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-60	-	-	V
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1	-	-3	V
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 125 \text{ °C}$	-	-	-50	μΑ
		V _{DS} = -48 V, V _{GS} = 0 V, T _J = 175 °C	-	-	-150	
On-state drain current ^a	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -10 V	-50	-	-	Α
		V _{GS} = -10 V, I _D = -17 A	-	0.012	0.015	
Duning and an atota projetoma 3		V _{GS} = -10 V, I _D = -50 A, T _J = 125 °C	-	-	0.025	0
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V, I _D = -50 A, T _J = 175 °C	-	-	0.030	Ω
		V _{GS} = -4.5 V, I _D = -14 A	-	-	0.020	
Forward transconductance ^a	9 _{fs}	V _{DS} = -15 V, I _D = -17 A	-	61	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	4950	-	pF
Output capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$	-	480	-	
Reverse transfer capacitance	C _{rss}		-	405	-	
Total gate charge ^c	Qg		-	110	165	
Gate-source charge ^c	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -50 \text{ A}$	-	19	-	nC
Gate-drain charge ^c	Q _{gd}		-	28	-	
Turn-on delay time ^c	t _{d(on)}		-	15	23	
Rise time ^c	t _r	V_{DD} = -30 V, R_L = 0.6 Ω	-	70	105	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong -50 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6 \Omega$	-	175	260	ns
Fall time ^c	t _f		-	175	260	
Source-Drain Diode Ratings and Ch	aracteristics (T _C = 25 °C) ^b		•		
Continuous current	Is		-	-	-50	۸
Pulsed current	I _{SM}		-	-	-80	Α
Forward voltage ^a	V _{SD}	$I_F = -50 \text{ A}, V_{GS} = 0 \text{ V}$	-	1	1.6	V
Reverse recovery time	t _{rr}	I _F = -50 A, di/dt = 100 A/μs	_	45	70	ns

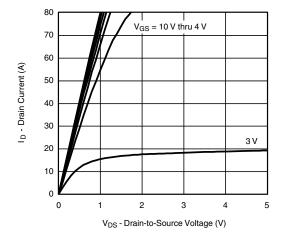
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

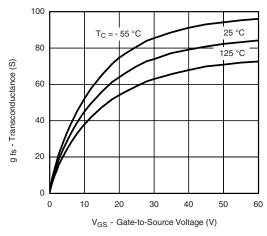
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



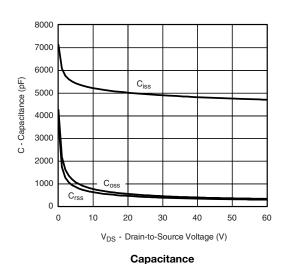
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

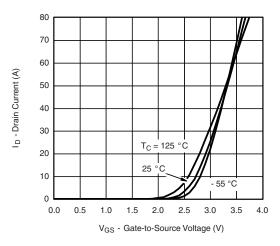


Output Characteristics

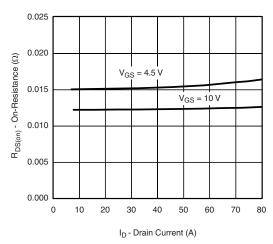


Transconductance

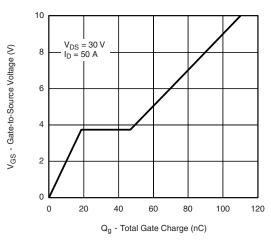




Transfer Characteristics



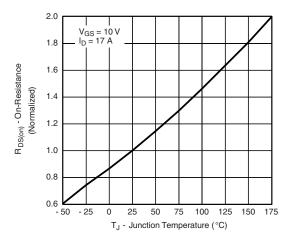
On-Resistance vs. Drain Current



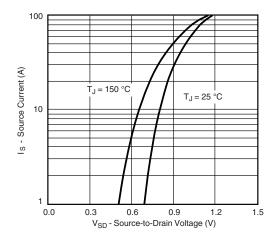
Gate Charge



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

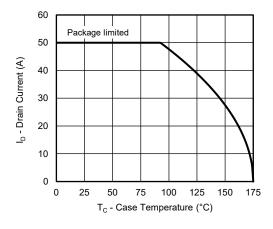


On-Resistance vs. Junction Temperature

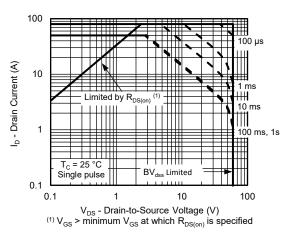


Source-Drain Diode Forward Voltage

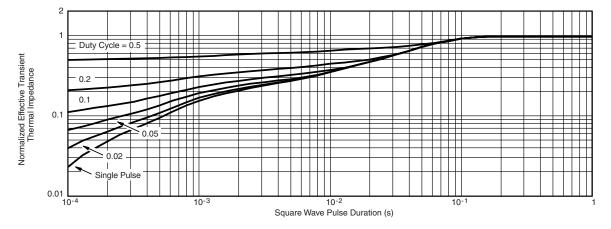
THERMAL RATINGS



Max. Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



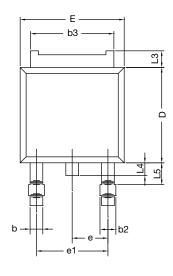
Normalized Thermal Transient Impedance, Junction-to-Case

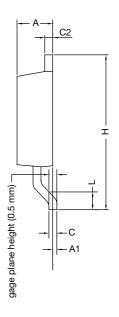
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for silicon technology and package reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72250.

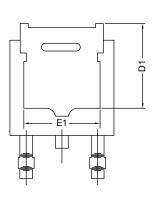


TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y







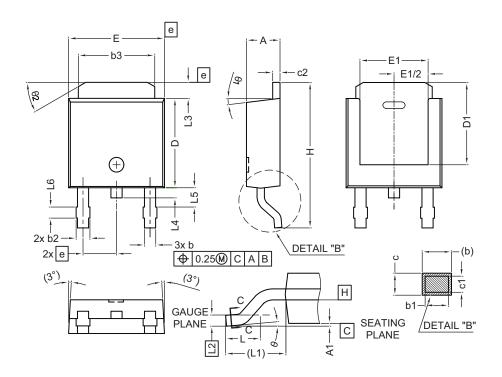
	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
Е	6.35	6.73	
E1	4.32	-	
Н	9.40	10.41	
е	2.28	BSC	
e1	4.56 BSC		
L	1.40	1.78	
L3	0.89	1.27	
L4	-	1.02	
L5	1.01	1.52	

Note

• Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	=	
Е	6.35	6.73	
E1	4.32	=	
е	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	ref.	
L2	0.51 BSC		
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

Notes

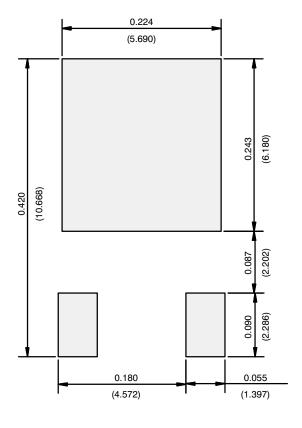
- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022

DWG: 5347



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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